

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ\text{C}$
20V	25m Ω @ $V_{GS} = 4.5\text{V}$	6.8A
	29m Ω @ $V_{GS} = 2.5\text{V}$	5.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, which make it ideal for high-efficiency power management applications.

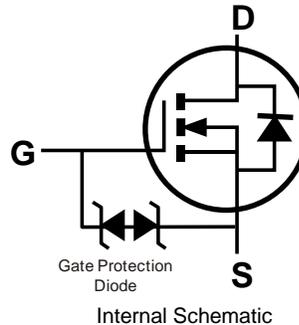
- Backlighting
- Power-Management Functions
- DC-DC Converters
- Motor Control



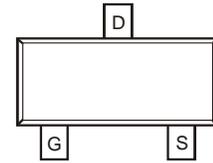
ESD-Protected Gate



Top View



Internal Schematic



Top View
Pin-out

Features and Benefits

- Low On-Resistance
- Low-Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN2024UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

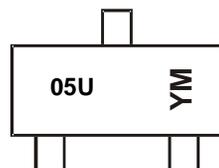
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2024UQ-7	SOT23	3,000/Tape & Reel
DMN2024UQ-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



05U = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: H = 2020)
 M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	H	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	6.8	A
		T _A = +70°C		5.5	
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	2.2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	45	A

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)		Steady State	R _{θJA}	159	°C/W
Total Power Dissipation (Note 6)			P _D	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)		Steady State	R _{θJA}	92	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	µA	T _J = +25°C, V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.5	—	0.9	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	16	25	mΩ	V _{GS} = 4.5V, I _D = 6.5A
			18.5	29		V _{GS} = 2.5V, I _D = 5.5A
			23	36		V _{GS} = 1.8V, I _D = 3.5A
Diode Forward Voltage	V _{SD}	—	0.8	1.2	V	V _{GS} = 0V, I _D = 5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	647	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	78	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	38	—	pF	
Gate Resistance	R _g	—	400	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	6.5	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Source Charge	Q _{gs}	—	1.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.7	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	98	—	ns	
Turn-On Rise Time	t _r	—	140	—	ns	V _{DS} = 10V, V _{GS} = 4.5V, R _L = 10Ω, R _g = 6Ω, I _D = 1A
Turn-Off Delay Time	t _{D(OFF)}	—	1024	—	ns	
Turn-Off Fall Time	t _f	—	434	—	ns	
Reverse Recovery Time	t _{RR}	—	245	—	ns	I _F = 1.0A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	149	—	nC	I _F = 1.0A, di/dt = 100A/µs

- Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high-coverage 2oz copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

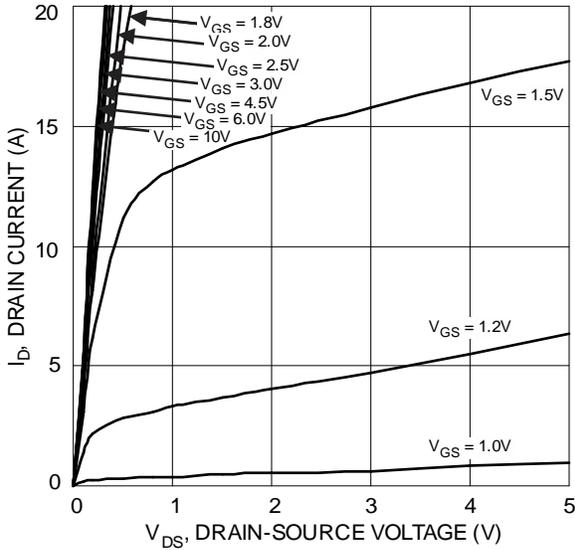


Figure 1 Typical Output Characteristic

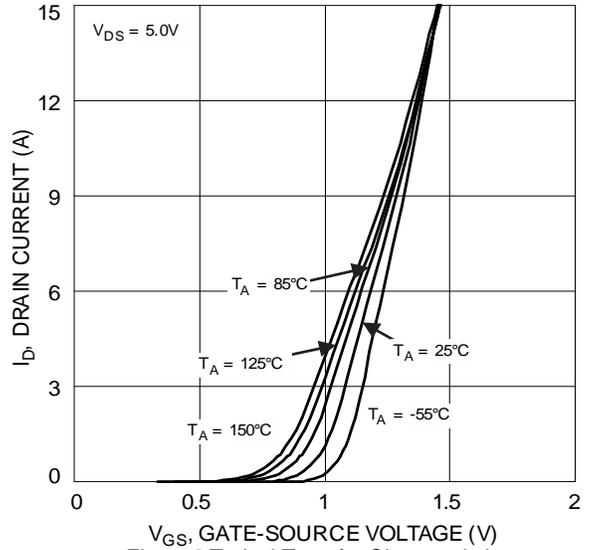


Figure 2 Typical Transfer Characteristics

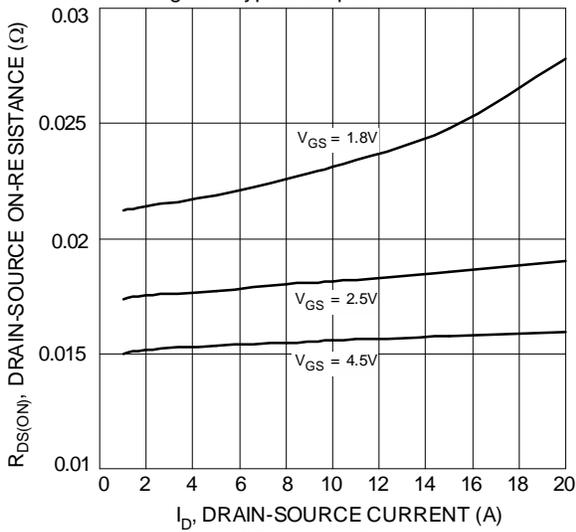


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

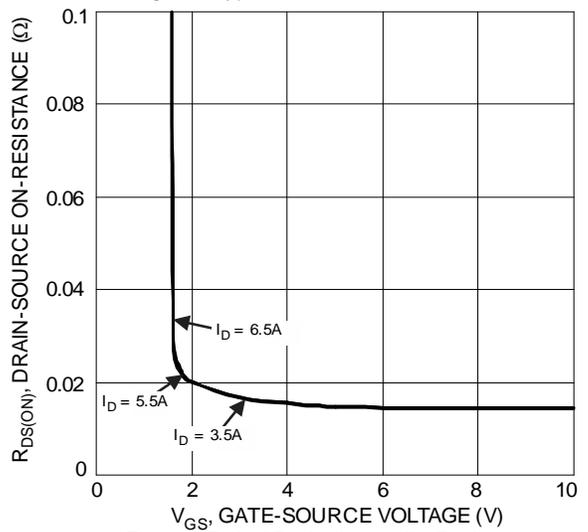


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

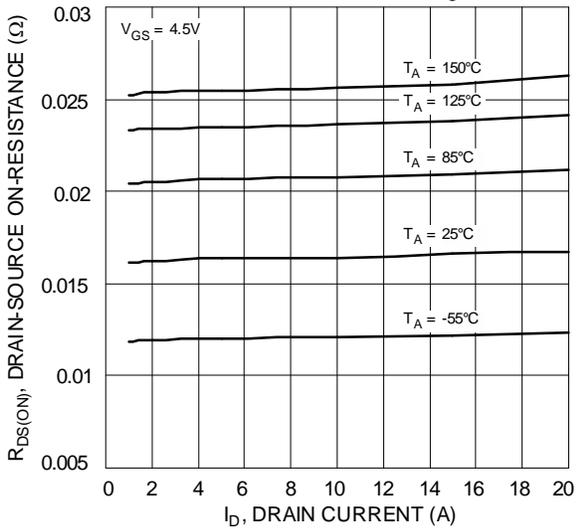


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

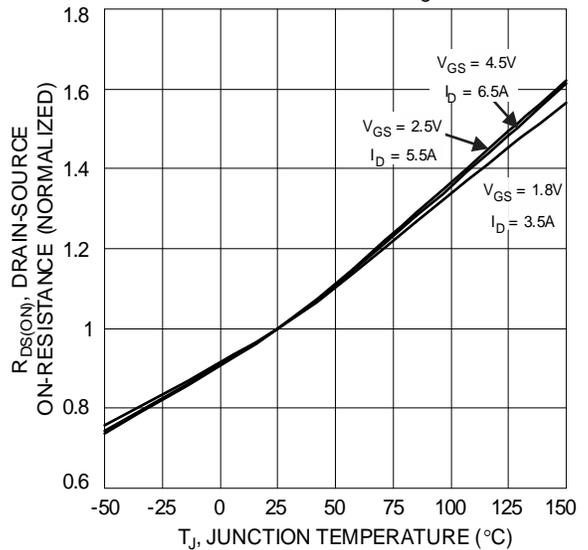


Figure 6 On-Resistance Variation with Temperature

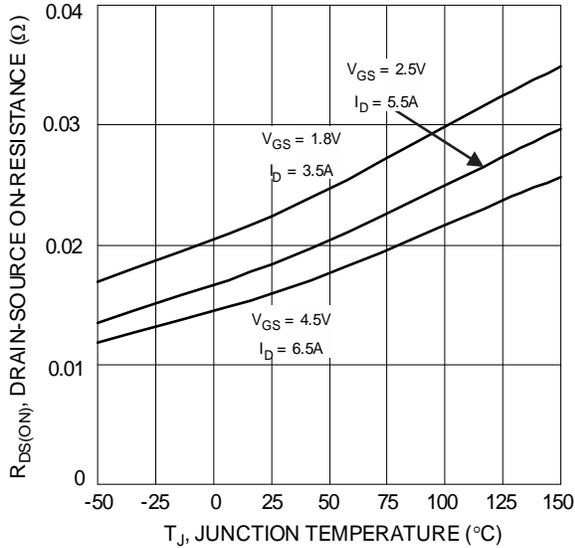


Figure 7 On-Resistance Variation with Temperature

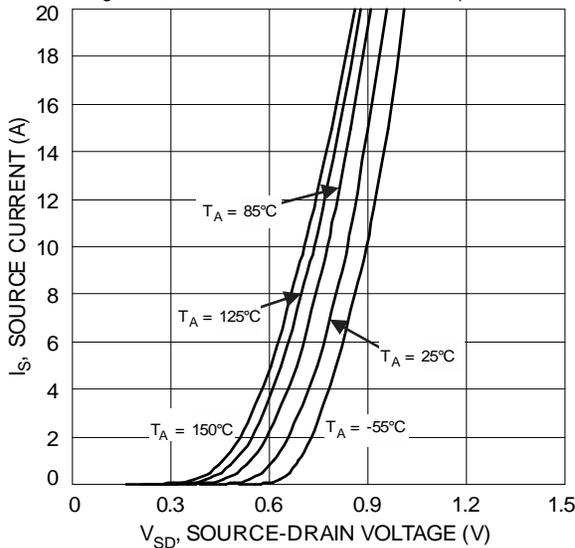


Figure 9 Diode Forward Voltage vs. Current

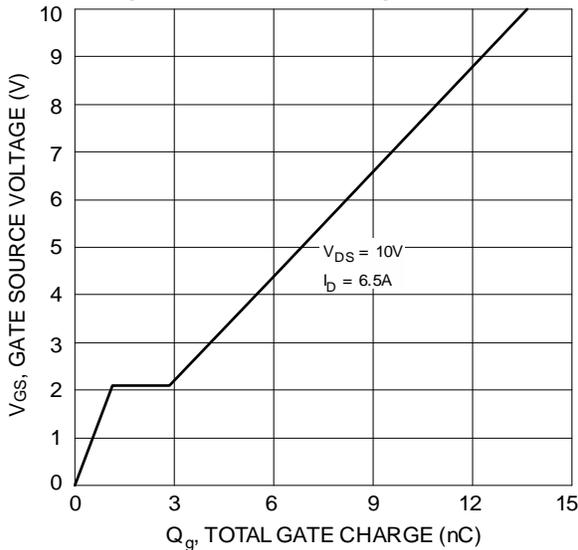


Figure 11 Gate Charge

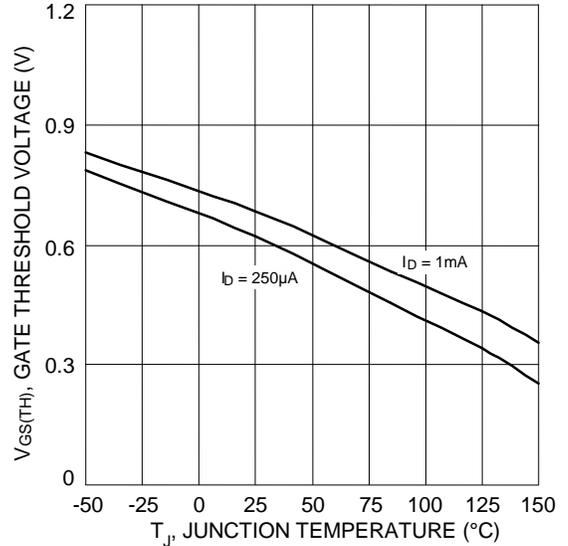


Figure 8 Gate Threshold Variation vs. Junction Temperature

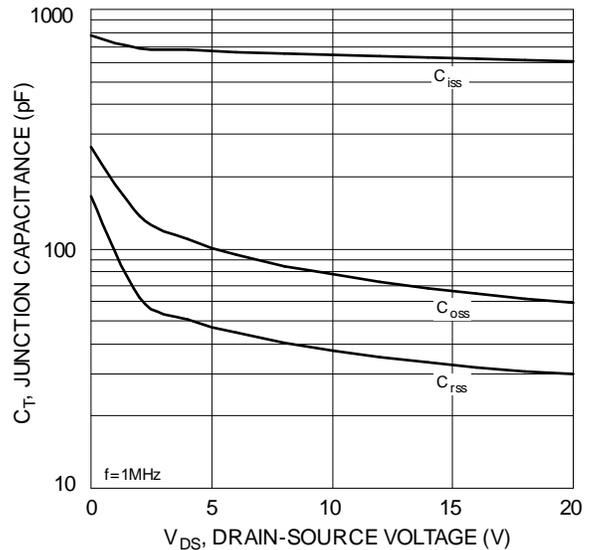


Figure 10 Typical Junction Capacitance

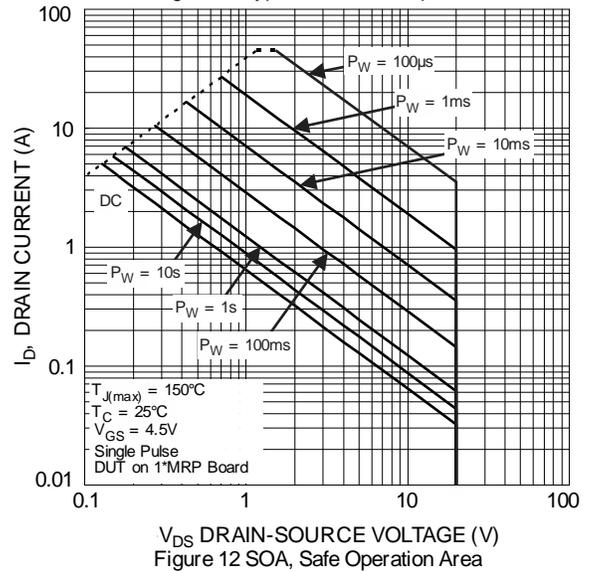


Figure 12 SOA, Safe Operation Area

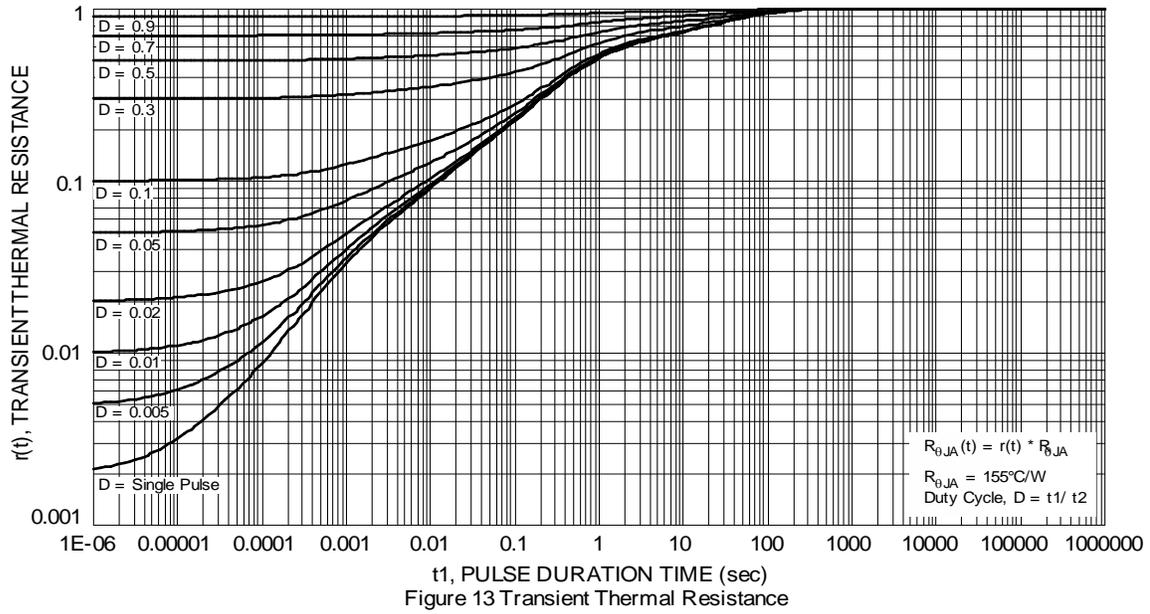
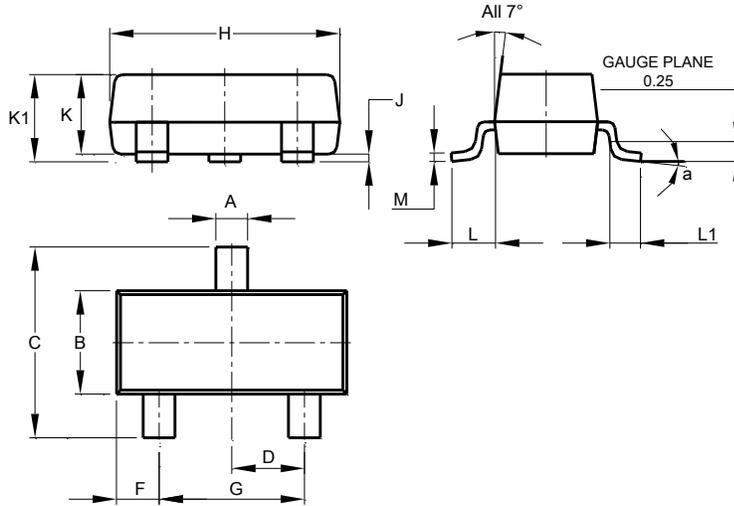


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

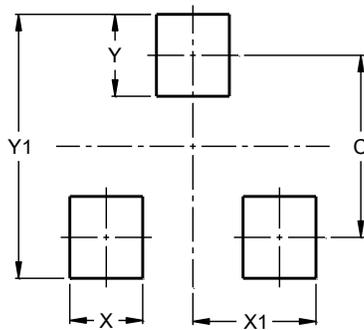


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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